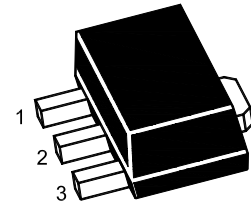


2SA2060U

PNP Silicon Epitaxial Planar Power Transistor

Applications

- For high speed switching, DC-DC converter and strobe



1.Base 2.Collector 3.Emitter
SOT-89 Plastic Package

Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

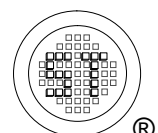
Parameter	Symbol	Value	Unit
Collector Base Voltage	$-V_{\text{CBO}}$	50	V
Collector Emitter Voltage	$-V_{\text{CEO}}$	50	V
Emitter Base Voltage	$-V_{\text{EBO}}$	7	V
Collector Current	$-I_{\text{C}}$	2	A
Peak Collector Current, Pulsed	$-I_{\text{CM}}$	3.5	A
Base Current	$-I_{\text{B}}$	200	mA
Collector Power Dissipation	P_{tot}	0.5 ¹⁾ 1 ²⁾	W
Junction Temperature	T_{j}	150	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	- 55 to + 150	$^\circ\text{C}$

Thermal Characteristics

Parameter	Symbol	Max.	Unit
Thermal Resistance from Junction to Ambient	$R_{\theta\text{JA}}$	250 ¹⁾ 125 ²⁾	$^\circ\text{C/W}$

¹⁾ Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.

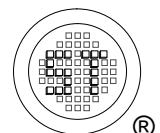
²⁾ Device mounted on FR-4 substrate PC board, 2oz copper, with 1-inch square copper plate.



2SA2060U

Characteristics at $T_a = 25^\circ\text{C}$

Parameter	Symbol	Min.	Typ.	Max.	Unit
DC Current Gain at $-V_{CE} = 2\text{ V}$, $-I_C = 300\text{ mA}$ at $-V_{CE} = 2\text{ V}$, $-I_C = 1\text{ A}$	h_{FE}	200 100	- -	500 -	- -
Collector Base Cutoff Current at $-V_{CB} = 50\text{ V}$	$-I_{CBO}$	-	-	100	nA
Emitter Base Cutoff Current at $-V_{EB} = 7\text{ V}$	$-I_{EBO}$	-	-	100	nA
Collector Base Breakdown Voltage at $-I_C = 100\text{ }\mu\text{A}$	$-V_{(BR)CBO}$	50	-	-	V
Collector Emitter Breakdown Voltage at $-I_C = 10\text{ mA}$	$-V_{(BR)CEO}$	50	-	-	V
Emitter Base Breakdown Voltage at $-I_E = 100\text{ }\mu\text{A}$	$-V_{(BR)EBO}$	7	-	-	V
Collector Emitter Saturation Voltage at $-I_C = 1\text{ A}$, $-I_B = 33\text{ mA}$	$-V_{CE(sat)}$	-	-	0.2	V
Base Emitter Saturation Voltage at $-I_C = 1\text{ A}$, $-I_B = 33\text{ mA}$	$-V_{BE(sat)}$	-	-	1.1	V
Collector Output Capacitance at $-V_{CB} = 10\text{ V}$, $f = 1\text{ MHz}$	C_{ob}	-	20	-	pF
Rise Time at $-V_{CC} \approx 30\text{ V}$, $I_{B1} = -I_{B2} = 33\text{ mA}$, $R_L = 30\text{ }\Omega$	t_r	-	60	-	ns
Storage Time at $-V_{CC} \approx 30\text{ V}$, $I_{B1} = -I_{B2} = 33\text{ mA}$, $R_L = 30\text{ }\Omega$	t_{stg}	-	250	-	ns
Fall Time at $-V_{CC} \approx 30\text{ V}$, $I_{B1} = -I_{B2} = 33\text{ mA}$, $R_L = 30\text{ }\Omega$	t_f	-	90	-	ns



2SA2060U

Electrical Characteristics Curves

Fig. 1 Output Characteristics Curve

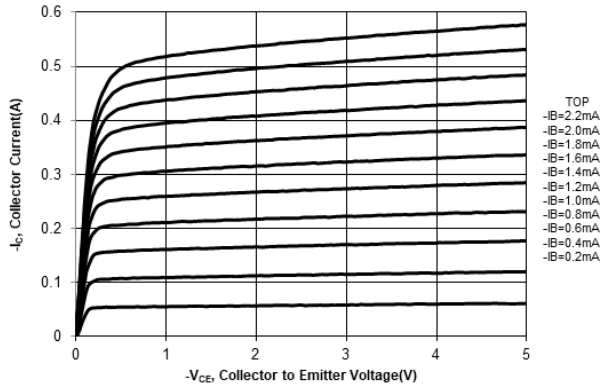


Fig. 2 Collector Current vs. Base to Emitter Voltage

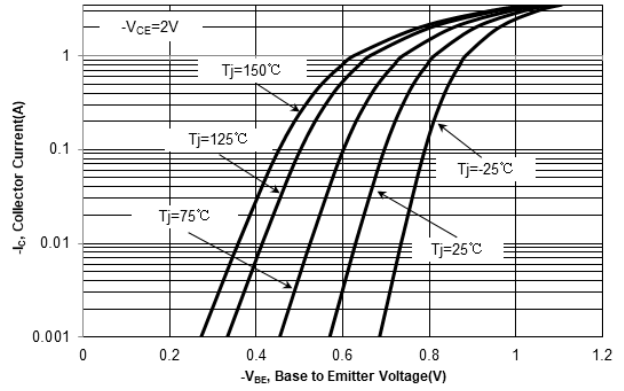


Fig. 3 DC Current Gain vs. Collector Current

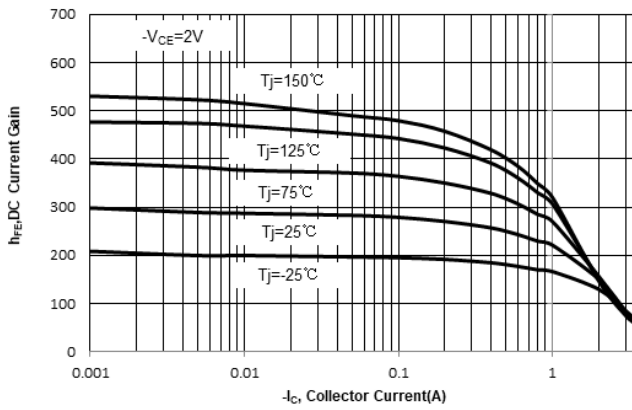
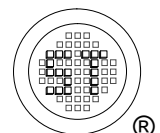
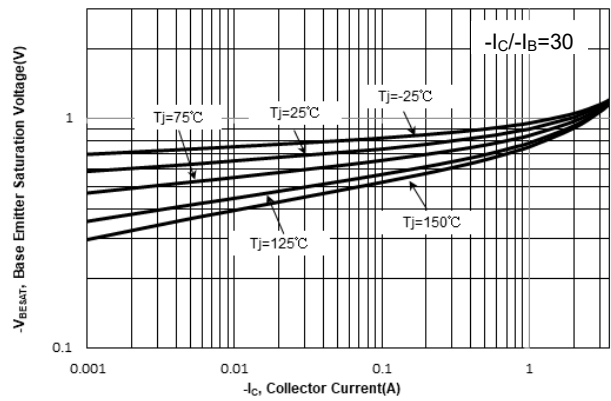


Fig. 4 $V_{BE(sat)}$ vs. Collector Current



2SA2060U

Electrical Characteristics Curves

Fig. 5 $V_{CE(sat)}$ vs. Collector Current

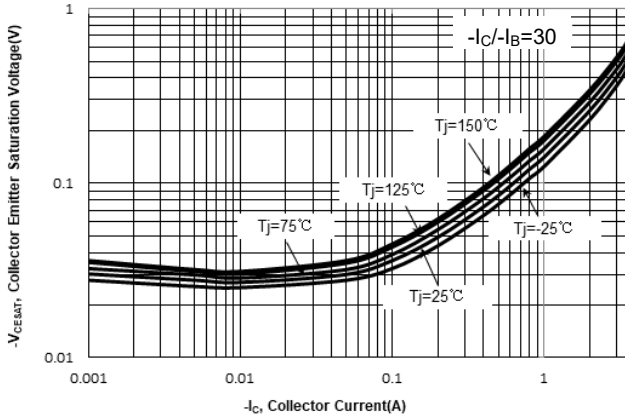


Fig. 6 Junction Capacitance

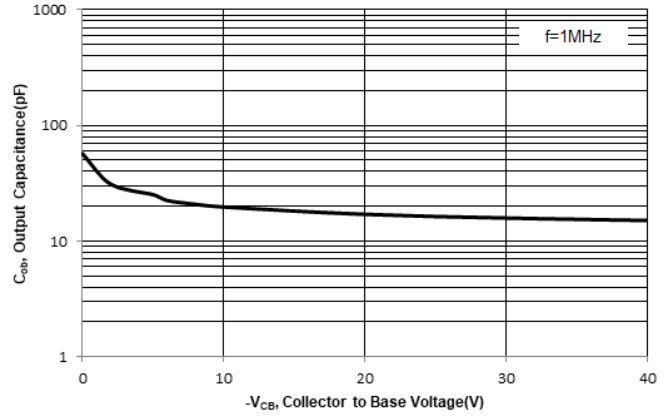
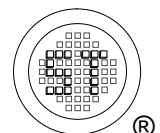
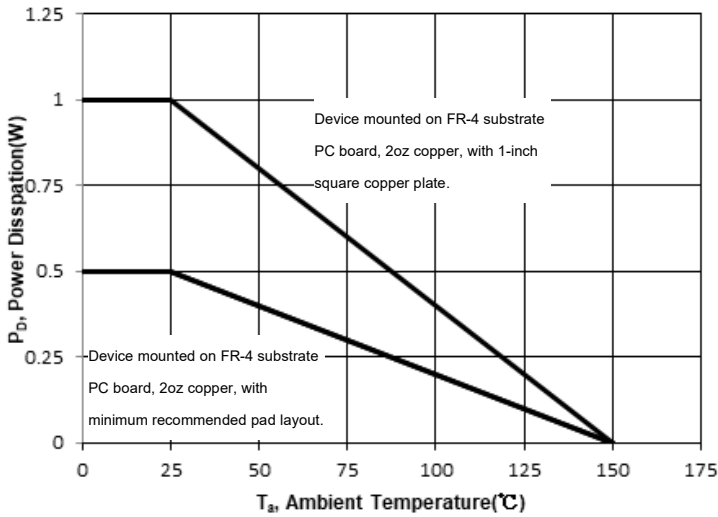


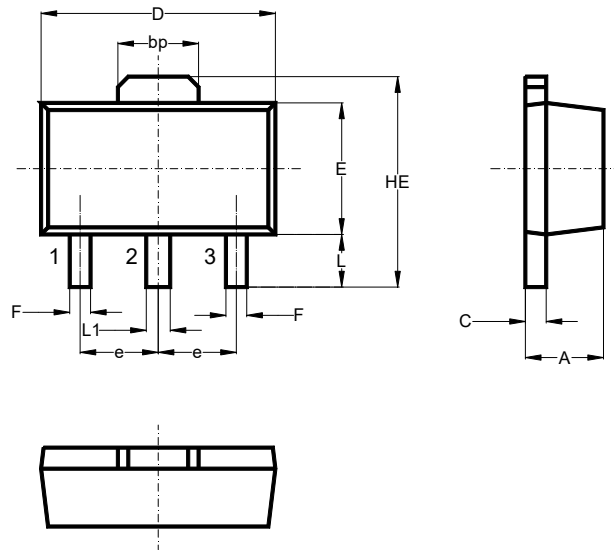
Fig. 7 Power Derating Curve



2SA2060U

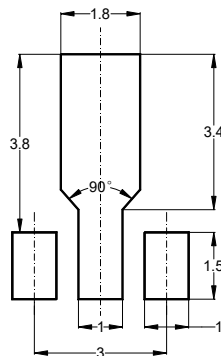
Package Outline (Dimensions in mm)

SOT-89



Unit	A	bp	C	D	E	F	HE	e	L	L1
mm	1.6	1.60	0.5	4.6	2.6	0.45	4.25	1.5	1.05	0.51
	1.4	1.50	0.3	4.4	2.4	0.35	3.75	typ.	0.95	0.41

Recommended Soldering Footprint



Packing information

Package	Tape Width (mm)	Pitch		Reel Size		Per Reel Packing Quantity
		mm	inch	mm	inch	
SOT-89	12	8 ± 0.1	0.315 ± 0.004	178	7	1,000
				330	13	4,000

Marking information

" 2SA2060U " = Part No.
 "YM" = Date Code Marking
 "Y" = Year
 "M" = Month
 Font type: Arial

